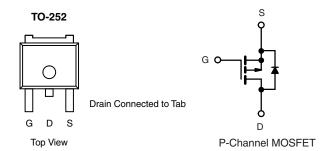


# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.010			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.024			
I <sub>D</sub> (A)	- 50			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- $\bullet$  100 %  $R_g$  and UIS Tested
- Material categorization:
   For definitions of compliance please see www.freescale.net.cn



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD45P03-12-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 30	V	
Gate-Source Voltage		$V_{GS}$	± 20	¬	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	1	- 50		
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 37		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 50	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 31		
Single Pulse Avalanche Energy	L = U. I IIIII	E <sub>AS</sub>	48	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	71	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	23	VV	
Operating Junction and Storage Temperatur	re Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	2.1	C/ VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	1				·	ı		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 30	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		- 2.0	- 2.5	\ \	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 125 °C	-	-	- 50	μA	
-		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 15 A	-	0.008	0.010	Ω	
Dunin Course On Chata Basistanas		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 15 A, T <sub>J</sub> = 125 °C	-	-	0.015		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 15 A, T <sub>J</sub> = 175 °C	-	-	0.017		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 12 A	-	0.019	0.024		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 17 A		-	34	-	S	
Dynamic <sup>b</sup>		<u> </u>						
Input Capacitance	C <sub>iss</sub>			-	2794	3495		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 15 V, f = 1 MHz	-	616	770	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	470	590		
Total Gate Charge <sup>c</sup>	Qg			-	55.3	83		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -45 \text{ A}$	-	7.3	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	14	-		
Gate Resistance	$R_g$	f = 1 MHz		1.40	2.86	4.50	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	16.5		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 0.33 $\Omega$ $I_D \cong$ - 45 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		-	11	16.5	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	29	43.5		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	19	28.5		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	•						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 200	Α	
Forward Voltage	V <sub>SD</sub>	$I_F = -40 \text{ A}, V_{GS} = 0$		-	- 0.9	- 1.5	V	

#### Notes

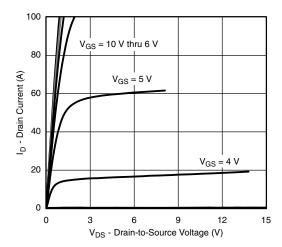
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

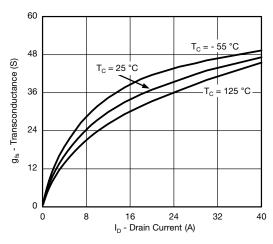


Automotive P-Channel 30 V (D-S) 175 °C MOSFET

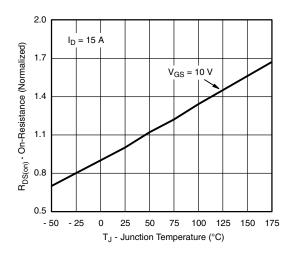
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \, ^{\circ}\text{C}$ , unless otherwise noted)



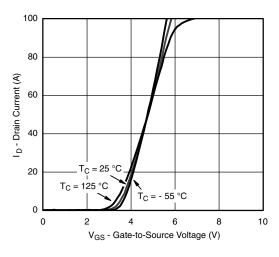
#### **Output Characteristics**



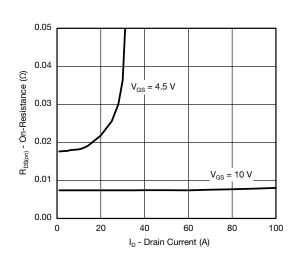
#### Transconductance



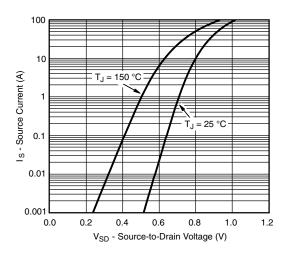
On-Resistance vs. Junction Temperature



#### **Transfer Characteristics**



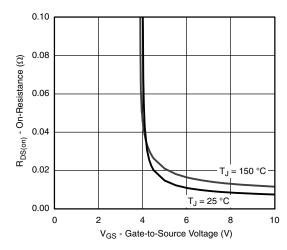
On-Resistance vs. Drain Current



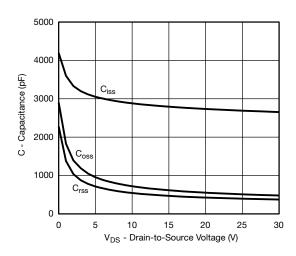
Source Drain Diode Forward Voltage

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

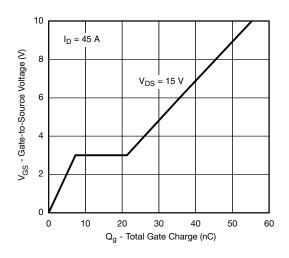
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \, ^{\circ}\text{C}$ , unless otherwise noted)



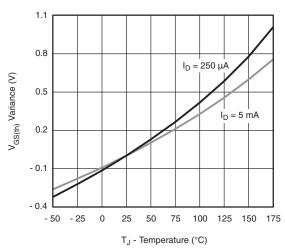
### On-Resistance vs. Gate-to-Source Voltage



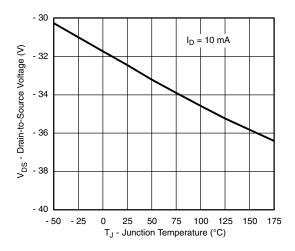
Capacitance



**Gate Charge** 



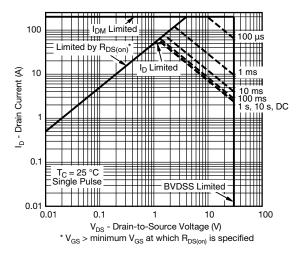
**Threshold Voltage** 



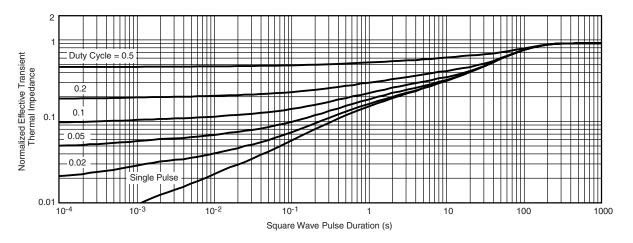
**Drain Source Breakdown vs. Junction Temperature** 

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



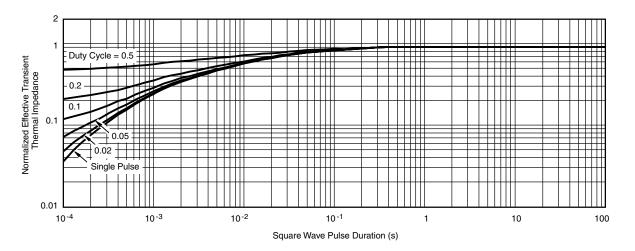
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



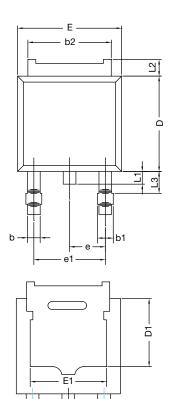
#### Normalized Thermal Transient Impedance, Junction-to-Case

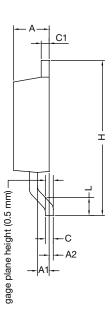
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

### **TO-252AA CASE OUTLINE**





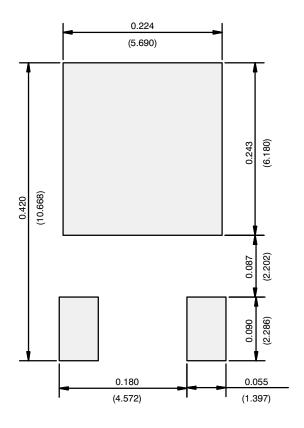
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

#### Note

• Dimension L3 is for reference only.

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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Automotive P-Channel 30 V (D-S) 175 °C MOSFET

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